

HD74BC645A

Octal Bus Transceivers With 3 State Outputs

REJ03D0291-0200Z (Previous ADE-205-027 (Z)) Rev.2.00 Jul.16.2004

Description

The HD74BC645A provides high drivability and operation equal to or better than high speed bipolar standard logic IC by using Bi-CMOS process. The device features low power dissipation that is about 1/5 of high speed bipolar logic IC. When the frequency is 10 MHz. The device has eight bus transceivers with three state outputs in a 20 pin package. Each device has an active low enable input (\overline{G}) and a direction control input, DiR. When DiR is high, data flows from the A inputs to the B outputs. When DiR is high, data flows from the B inputs to the A outputs. When enable inputs (\overline{G}) is high, disables both A and B ports by placing then in a high impedance.

Features

- Input/Output are at high impedance state when power supply is off.
- Input pins can be open, when not used, owing to built in input pull up circuit.
- Input is TTL level.
- Wide operating temperature range $Ta = -40 \text{ to } +85^{\circ}\text{C}$.
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74BC645AFPEL	SOP-20 pin (JEITA)	FP-20DAV	FP	EL (2,000 pcs/reel)

Function Table

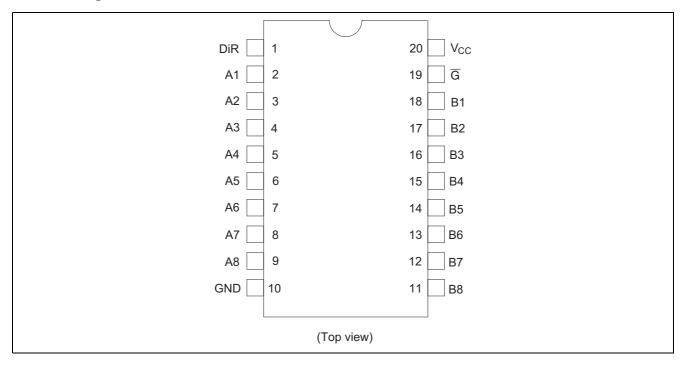
Control Inputs		
G	DIR	Operation
L	L	B data to A bus
L	Н	A data to B bus
Н	X	Z

H: High levelL: Low levelX: ImmaterialZ: High impedance





Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage	V _{cc}	-0.5 to +7.0	V
Input diode current	I _{IK}	±30	mA
Input voltage	V _{IN}	-0.5 to +7.5	V
Output voltage	V _{OUT}	-0.5 to +7.5	V
Off state output voltage	$V_{OUT(off)}$	-0.5 to +5.5	V
Storage temperature	Tstg	-65 to +150	°C

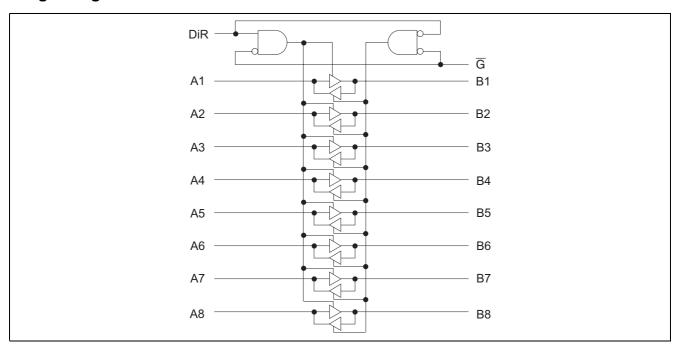
Note: 1. The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Min	Тур	Max	Unit
Supply voltage	V _{cc}	4.5	5.0	5.5	V
Input voltage	V _{IN}	0	_	V_{cc}	V
Ouput voltage	V _{OUT}	0	_	V_{cc}	V
Operating temperature	Topr	-40	_	85	°C
Input rise/fall time*1	t _r , t _f	0	_	8	ns/V

Note: 1. This item guarantees maximum limit when one input switches. Waveform: Refer to test circuit of switching characteristics.

Logic Diagram



Electrical Characteristics (Ta = -40 to +85°C)

Item	Symbol	V _{cc} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}		2.0	_	V	
	V_{IL}		_	0.8	V	
Output voltage	V _{OH}	4.5	2.4	_	V	$I_{OH} = -3 \text{ mA}$
		4.5	2.0	_	V	$I_{OH} = -15 \text{ mA}$
	V_{OL}	4.5	_	0.5	V	$I_{OL} = 48 \text{ mA}$
		4.5	_	0.55	V	I _{OL} = 64 mA
Input diode voltage	V_{IK}	4.5	_	-1.2	V	$I_{IN} = -18 \text{ mA}$
Input current	I ₁	5.5	_	-250	μA	$V_{IN} = 0 V$
		5.5	_	100	μA	An or Bn, $V_{IN} = 5.5 \text{ V}$
		5.5	_	1.0	μΑ	DiR or \overline{G} , $V_{IN} = 5.5 \text{ V}$
		5.5	_	100	μA	DiR or \overline{G} , $V_{IN} = 7 V$
Output short circuit current*1	Ios	5.5	-100	-225	mA	$V_0 = 0 \text{ V}, V_{IN} = 0 \text{ or } 5.5 \text{ V}$
Off state output current	I _{OZH}	5.5	_	-100	μA	$V_0 = 2.7 \text{ V}$
	I _{OZL}	5.5	_	-250	μΑ	$V_0 = 0.5 \text{ V}$
Supply current	I _{CCL}	5.5	_	31.5	mA	$V_{IN} = 0 \text{ or } 5.5 \text{ V}$
						All outputs is "L"
	I _{CCH}	5.5	_	0.5	mA	$V_{IN} = 0 \text{ or } 5.5 \text{ V}$
						All outputs is "H"
	I _{CCZ}	5.5	_	4.5	mA	$V_{IN} = 0 \text{ or } 5.5 \text{ V}$
						All outputs is "Z"
	I _{CCT} * ²	5.5	_	1.5	mA	$V_{IN} = 3.4 \text{ or } 0.5 \text{ V}$

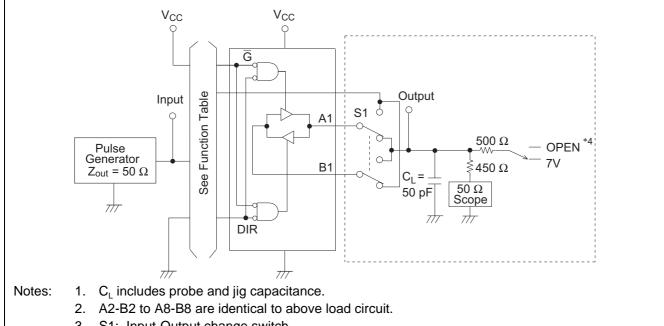
Notes: 1. Not more than one output should be shorted at a time and duration of the short circuit should not exceed one second.

2. When input by the TTL level, it shows $\rm I_{\rm CC}$ increase at per one input pin.

Switching Characteristics ($C_L = 50 \text{ pF}$)

		Ta = 25°C		Ta = -40	Ta = -40 to +85°C			
		$V_{cc} = 5.0 V$		$V_{cc} = 5.0 \text{ V } \pm 10\%$				
Item	Symbol	Min	Max	Min	Max	Unit	Test Conditions	
Propagation delay time	t _{PLH}	3.0	6.0	3.0	7.0	ns	An to Bn	
	t _{PHL}	3.0	6.0	3.0	7.0			
	t _{PLH}	3.0	6.0	3.0	7.0	ns	Bn to An	
	t _{PHL}	3.0	6.0	3.0	7.0			
Output enable time	t _{zH}	3.0	9.0	3.0	11.0	ns	G to Bn	
	t _{ZL}	3.0	9.0	3.0	11.0			
	t _{zH}	3.0	9.0	3.0	11.0	ns	G to An	
	t _{ZL}	3.0	9.0	3.0	11.0			
Output disable time	t _{HZ}	3.0	8.0	3.0	10.0	ns	G to Bn	
	t _{LZ}	3.0	8.0	3.0	10.0			
	t _{HZ}	3.0	8.0	3.0	10.0	ns	G to An	
	t _{LZ}	3.0	8.0	3.0	10.0			
Input capacitance	C _{IN}	3.0 (Typ)		_		pF	V _{IN} = V _{CC} or GND	
Output capacitance	C _{I/O}	15.0 (Typ)		_		pF	$V_{I/O} = V_{CC}$ or GND	

Test Circuit

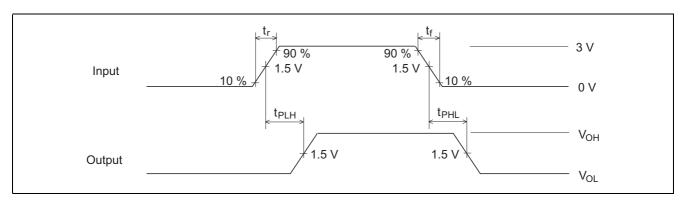


3. S1: Input-Output change switch.

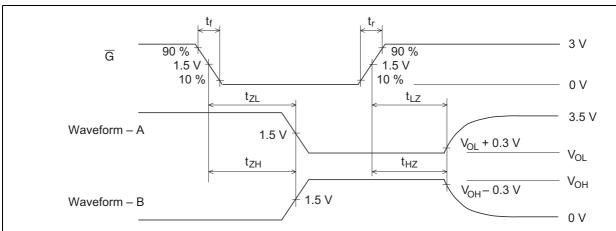
4. Open: t_{PLH} , t_{PHL} , t_{ZH} t_{HZ}

7 V: t_{ZL} , t_{LZ}

Waveforms-1



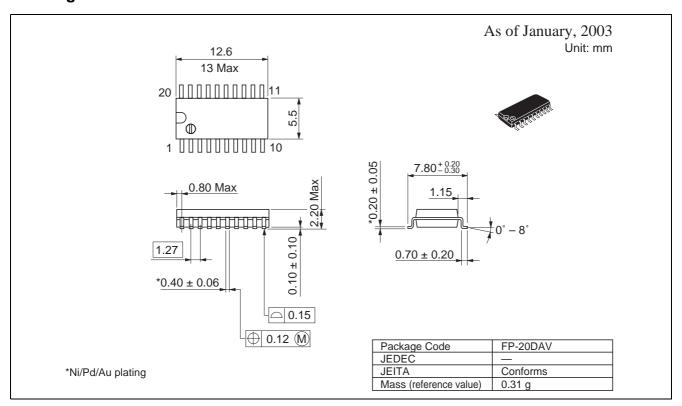
Waveforms-2



Notes:

- 1. $t_r = 2.5 \text{ ns}, t_f = 2.5 \text{ ns}$
- 2. Input waveforms: PRR = 1 MHz, duty cycle 50%
- 3. Waveform-A shows input conditions such that the output is "L" level when enable by the output control.
- 4. Waveform-B shows input conditions such that the output is "H" level when enable by the output control.

Package Dimensions



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